Amendments to the Claims

1. (previously amended): A method of fabricating an integrated circuit, comprising the steps of:

forming a seed layer over a semiconductor body;

performing a wet surface treatment on said seed layer, wherein said step of performing a wet surface treatment comprises the step of rinsing said seed layer with an aqueous solution comprising a solution selected from the group consisting of isopropyl alcohol and de-ionized (DI)-water, acetone and DI-water, methyl alcohol and DI-water, ethyl alcohol and DI-water, and acetic acid and DI-water; and

after performing said wet surface treatment, depositing a copper layer on said seed layer using electrochemical deposition (ECD).

2. (original): The method of claim 1, wherein said step of performing a wet surface treatment occurs in a plating cell of an ECD tool.

3. (original): The method of claim 2, wherein said step of performing a wet surface treatment comprises the step of rinsing said seed layer with a water-based solution for a duration in the range of 1-5 seconds.

4. (original): The method of claim 1, wherein said step of performing a wet surface treatment occurs in a cell separate from a plating cell of an ECD tool.

5. (original): The method of claim 4, wherein said step of performing a wet surface treatment comprises the step of rinsing said seed layer with a water-based solution for a duration in the range of 1-15 seconds.

6. (original): The method of claim 1, wherein said step of performing a wet surface treatment occurs in a tool separate from an ECD tool used to deposit said copper layer.

7. (original): The method of claim 6, wherein said step of performing a wet surface treatment comprises the step of rinsing said seed layer with a water-based solution for a duration in the range of 1-15 seconds.

8. (cancelled)

9. (amended): The method of claim ~~8~~1, wherein the step of performing a wet surface treatment further comprises the step of spin-drying said seed layer after said rinsing step.

10. (amended): The method of claim ~~8~~1, wherein the step of performing a wet surface treatment further comprises the step of drying said seed layer with N_2.

11. (amended): The method of claim ~~8~~1, wherein said aqueous solution comprises de-ionized water.

12. (cancelled)

13. (previously amended): A method of fabricating a copper interconnect for an integrated circuit comprising the steps of:

providing a semiconductor body having a dielectric layer with a trench formed therein;

forming a barrier layer over said dielectric layer including within said trench;

forming a seed layer over said barrier layer;

rinsing said seed layer with a water-based solution, wherein said water-based solution is selected from the group consisting if isopropyl alcohol and deionized (DI) water, acetone and DI-water, methyl alcohol and DI-water, ethyl alcohol and DI-water, and acetic acid and DI-water;

after said rinsing step, electrochemically depositing a copper layer on said seed layer; and

chemically-mechanically polishing said copper layer to form said copper interconnect in said trench.

14. (original): The method of claim 13, wherein said rinsing step occurs in a plating cell of an ECD tool and has a duration in the range of 1-5 seconds.

15. (original): The method of claim 13, wherein said rinsing step occurs in a cell separate from a plating cell of an ECD tool and has a duration in the range of 1-15 seconds.

16. (original): The method of claim 13, wherein said rinsing step occurs in a tool separate from an ECD tool used to deposit said copper layer and has a duration in the range of 1-15 seconds.

17. (original): The method of claim 13 further comprising the step of spin-drying said seed layer after said rinsing step.

18. (original): The method of claim 13, wherein said water-based solution comprises de-ionized water.

19. (original): The method of claim 13, further comprising the step of drying said seed layer with N_2 after said rinsing step.

20. (Cancelled)

21. (Cancelled)